



Bay Linear
Linear Excellence

POWER MOSFET

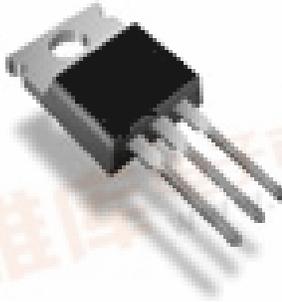
IRF830

Advance Information

Description

The Bay Linear MOSFET's provide the designers with the best combination of fast switching, ruggedized device design, low On-resistance and low cost-effectiveness.

The TO-220 is offered in a 3-pin is universally preferred for all commercial-industrial applications at power dissipation level to approximately to 50 watts. Also, available in a D² surface mount power package with a power dissipation up to 2 Watts



Features

- **Dynamic dv/dt Rating**
- **Repetitive Avalanche Rated**
- **Fast Switching**
- **Ease of Paralleling**
- **Simple Drive Requirements**

$V_{DSS} = 500V$

$R_{DS(ON)} = 1.5 \Omega$

$I_D = 4.5A$

Ordering Information

Device	Package	Temp.
IRL830T	TO-220	0 to 150°C
IRL830S	TO-263 (D ²)	0 to 150°C

Absolute Maximum Rating

	Parameter	Max	Unit
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	4.5	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	2.9	
I_{DM}	Pulsed Drain Current (1)	18	
$P_D @ T_C = 25^\circ C$	Power Dissipation	74	W
	Linear Derating Factor	0.59	W/°C
	Linear Derating Factor (PCB Mount, D ²) (1)	0.025	
V_{GS}	Gate-to- Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy (2)	280	mJ
I_{AR}	Avalanche Current (1)	4.5	A
E_{AR}	Repetitive Avalanche Energy (1)	7.4	mJ
dv/dt	Peak Diode Recovery dv/dt (3)	3.5	V/ns
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to +150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Min	Typ	Max	Units
$R_{\theta JC}$	Junction-to Case	-	-	1.7	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface (TO-220)	-	0.50		
$R_{\theta JA}$	Junction-to Ambient (PCB Mount, D ²)	-	-	40	
$R_{\theta JA}$	Junction-to Ambient	-	-	62	



Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$V_{(BR)DSS}$	Drain-to-source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	500			V
$V_{(BR)DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	Reference to 25°C , $I_D = 1mA$	-	0.61	-	V/ $^\circ\text{C}$
$I_{D(ON)}$	On-State Drain Current (note 2)	$V_{GS} > I_{D(ON)} \times R_{DS(ON)Max}$			4.5	A
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	$V_{GS} = 10V, I_D = 2.7A$ (note 4)			1.5	Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	V
g_{fs}	Forward Transconductance	$V_{DS} = 50V, I_D = 2.7A$	2.5	-	-	S
I_{DSS}	Drain-to-Source Leakage Current	$V_{DS} = 500V, V_{GS} = 0V$	-	-	25	μA
		$V_{DS} = 400V, V_{GS} = 0V,$ $T_C = 125^\circ\text{C}$	-	-	250	
I_{GSS}	Gate-to-Source Forward Leakage	$V_{GS} = 20V$	-	-	100	nA
	Gate-to-Source Reverse Leakage	$V_G = -20V$	-	-	-100	
Q_g	Total Gate Charge	$I_D = 3.1A$	-	-	38	nC
Q_{gs}	Gate-to-Source Charge	$V_{DS} = 400V$	-	-	5.0	
Q_{gd}	Gate-to-Drain ("Miller") Charge	$V_{GS} = 10V$ (note 4)	-	-	22	
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 250V$ $I_D = 3.1A$ $R_G = 12\Omega$ $R_D = 79\Omega$ (note 4)	-	8.2	-	ns
T_r	Rise Time		-	16	-	
$t_{d(off)}$	Turn -Off Delay Time		-	42	-	
T_f	Fall Time		-	16	-	
L_D	Internal Drain Inductance	Between lead 6mm (0.25in.) from package and center or die contact	-	4.5	-	nH
L_S	Internal Source Inductance		-	7.5	-	
C_{iss}	Input Capacitance	$V_{GS} = 0V$	-	610	-	pF
C_{oss}	Output Capacitance	$V_{DS} = 25V$	-	160	-	
C_{rss}	Reverse Transfer Capacitance	$F = 1.0MHz$	-	68	-	

Source-Drain Rating Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Units
I_S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode.	-	-	4.5	A
I_{SM}	Pulsed Source Current (Body Diode) (Note 1)		-	-	18	
V_{SD}	Diode Forward Voltage (note 4)	$T_J = 25^\circ\text{C}, I_S = 2.5A, V_{GS} = DV$	-	-	1.6	V
t_{rr}	Reverse Recovery Time	$T_J = 25^\circ\text{C}, I_F = 2.1A$	-	320	640	ns
Q_{rr}	Reverse Recovery Charge	$di/dt = 100A/\mu s$ (Note 4)	-	1.0	2.0	μC
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $(L_S + L_D)$)				

Notes: 1. Repetitive Rating; pulse width limited by max. junction temperature.

2. $V_{DD} = 50V$, starting $T_J = 25^\circ\text{C}$, $L = 24\text{ mH}$ $R_G = 25\Omega$, $I_{AS} = 4.5A$

3. $I_{SD} \leq 4.5A$, $di/dt \leq 75A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$

4. Pulse with $\leq 300\mu s$; duty cycle $\leq 2\%$

Advance Information- These data sheets contain descriptions of products that are in development. The specifications are based on the engineering calculations, computer simulations and/ or initial prototype evaluation.

Preliminary Information- These data sheets contain minimum and maximum specifications that are based on the initial device characterizations. These limits are subject to change upon the completion of the full characterization over the specified temperature and supply voltage ranges.

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